

HMP065N180C

650-V Cascode GaN HEMT

Description

These GaN HEMT utilize a GaN transistor technologies to provide low $R_{DS(on)}$ and using the Cascode in the TO220 package to realize the normal-off high electron mobility transistor.

Also provides high breakdown voltage, high current and high operating speed which is suitable for high power applications.

Features

- Gate drive voltage compatibility (-20V to 20V)
- High operating frequency
- Low Q_{rr}

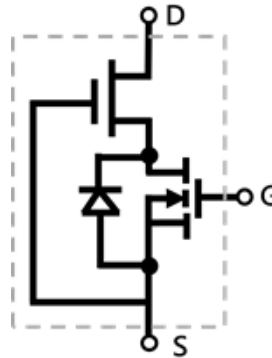
Typical Applications

- Switch Mode Power Supplies (SMPS)
- AC-DC/ DC-DC Converters
- Motor Drives

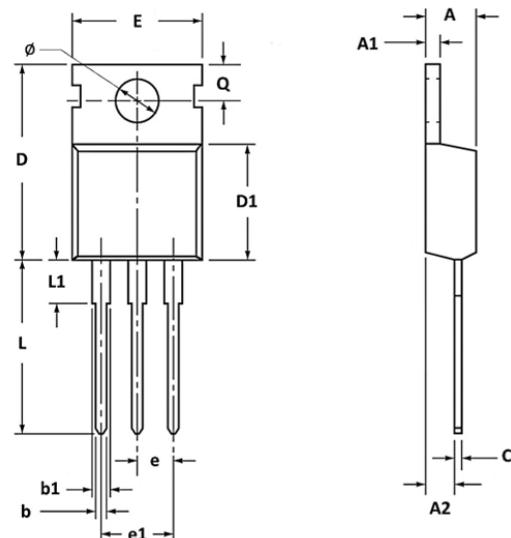
Package type : TO220



Graphic Symbol

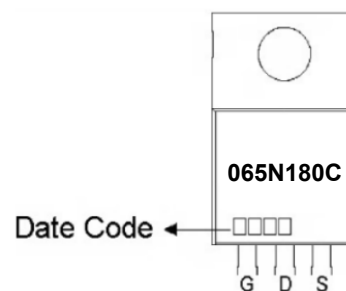


Package Dimension



SYMBOL	DIMENSION (mm)		SYMBOL	DIMENSION (mm)	
	MIN.	MAX.		MIN.	MAX.
A	4.20	4.80	E	9.70	10.40
A1	1.10	1.50	e	2.54(ref.)	
A2	2.20	3.00	e1	5.08(ref.)	
b	0.60	1.00	L	12.70	14.50
b1	1.20	1.80	L1	2.60	4.10
C	0.30	0.65	Φ	3.40	4.00
D	14.30	16.00	Q	2.50	3.00
D1	8.30	9.40			

Marking



RoHS Compliant

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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V_{DS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	-20 / +20	V
P_{tot}	Total Power dissipation @ $T_C = 25^\circ\text{C}$	83	W
I_D	Continuous Drain Current at $T_C = 25^\circ\text{C}$	16.1	A
	Continuous Drain Current at $T_C = 100^\circ\text{C}$	11.3	A
$I_{D\ pulse}$	Pulse Drain Current (Pulse width = 10 μs) ²	60.4	A
T_J/T_{STG}	Operating Junction and Storage Temperature	-55...150	$^\circ\text{C}$
T_{SOLD}	Soldering peak temperature	260	$^\circ\text{C}$

Notes

1. In off-state, spike duty cycle $D < 0.01$, spike duration $< 1\ \mu\text{s}$
2. Value is not tested to full current in production.

Thermal Resistance Ratings

Symbol	Parameter	Maximum	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient	50	$^\circ\text{C/W}$
$R_{\theta JC}$	Maximum Junction-to-Case	1.5	$^\circ\text{C/W}$

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Static Electrical Characteristics, ($T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=10\text{V}$, $I_D=1\text{mA}$	-	1.7	3.0	V
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$	650	-	-	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=650\text{V}$, $V_{GS}=0\text{V}$, $T_J=25^\circ\text{C}$	-	2.5	30	μA
		$V_{DS}=650\text{V}$, $V_{GS}=0\text{V}$, $T_J=150^\circ\text{C}$	-	10	-	
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=5\text{A}$, $T_J=25^\circ\text{C}$	-	146	180	$\text{m}\Omega$
		$V_{GS}=10\text{V}$, $I_D=5\text{A}$, $T_J=150^\circ\text{C}$	-	296	-	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20\text{V}$	-	-	± 100	nA

AC Electrical Characteristics, ($T_J=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
C_{ISS}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=400\text{V}$, $f=100\text{kHz}$	-	846	-	pF
C_{OSS}	Output Capacitance		-	23.2	-	
C_{RSS}	Reverse Transfer Capacitance		-	4.2	-	
Q_g	Total Gate Charge	$V_{DS}=400\text{V}$, $V_{GS}=0$ to 10V , $I_{DS}=5\text{A}$	-	8.3	-	nC
Q_{GS}	Gate-Source Charge		-	2.7	-	
Q_{OSS}	Output Charge	$V_{GS}=0\text{V}$, $V_{DS}=0\sim 400\text{V}$	-	33	-	
Q_{RR}	Reverse Recovery Charge	$I_S=5\text{V}$, $V_{DS}=0\text{V}$	-	48	-	
$t_{d(on)}$	Turn-On Delay Time	$V_{DD}=400\text{V}$, $V_{GS}=0$ to 10V , $I_{DS}=2\text{A}$, $R_{G(on)}=25\Omega$,	-	10	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	20	-	
P_D	Maximum power dissipation	$T_c=25^\circ\text{C}$	-	83	-	W

- Typical Electrical Characteristics

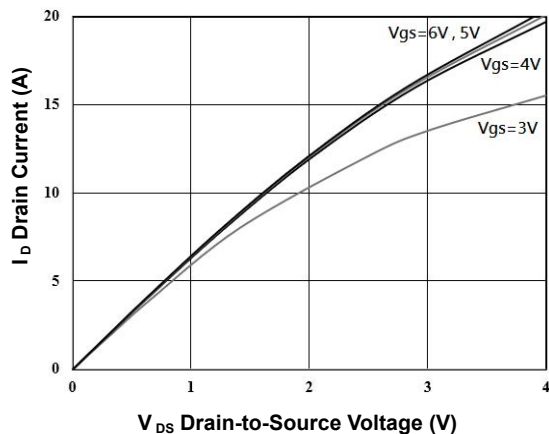


FIG.1-Output Characteristics $T_J=25^\circ\text{C}$

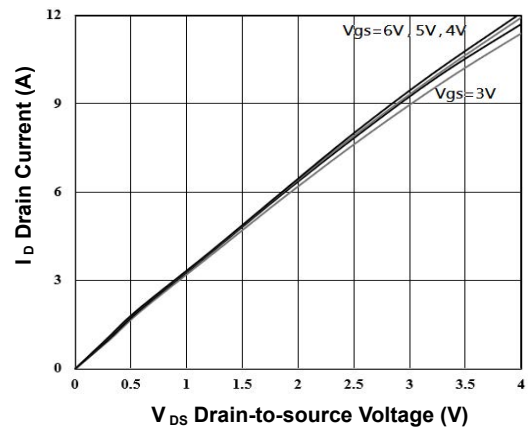


FIG.2- Output Characteristics $T_J=150^\circ\text{C}$

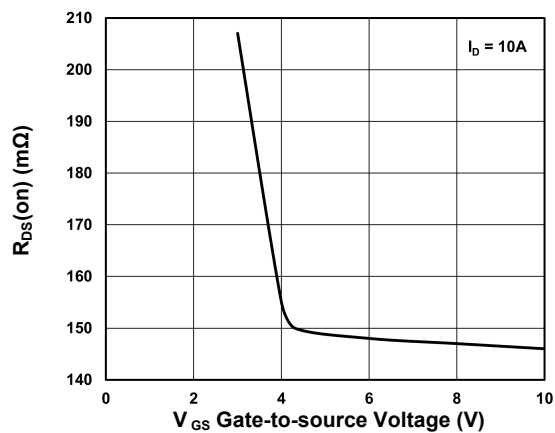


FIG.3- Resistance vs V_{GS}

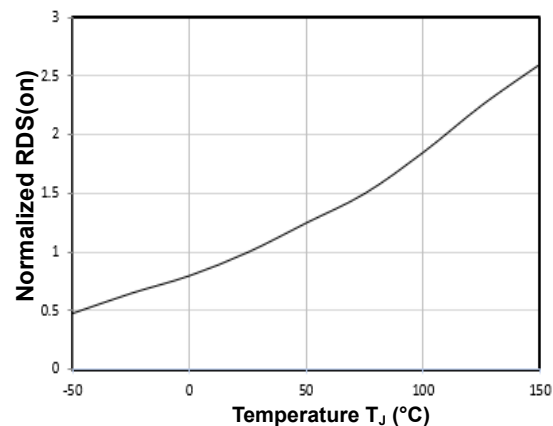


FIG.4- Normalized $R_{DS(on)}$ vs. Temperature

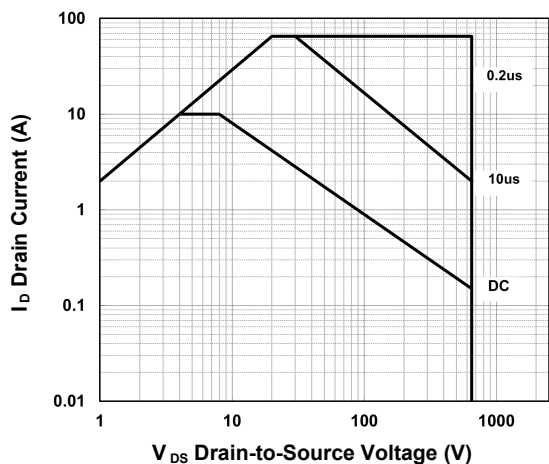


FIG.5- Safe Operating Area

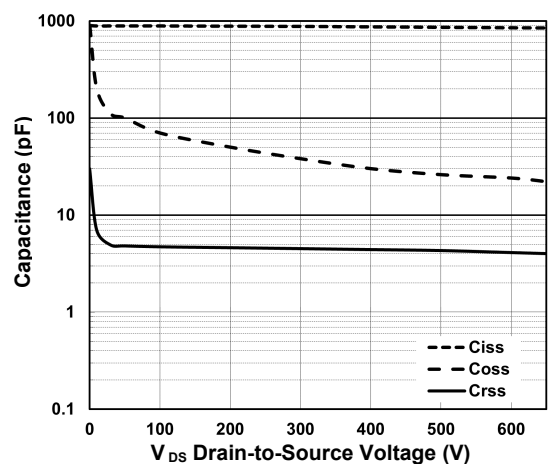


FIG.6- Capacitance vs Drain-Source Voltage

- Typical Electrical Characteristics

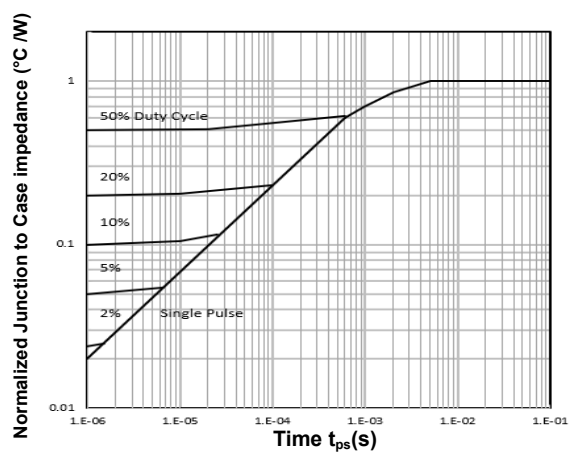


FIG.7- Transient Thermal impedance (Junction to Case)

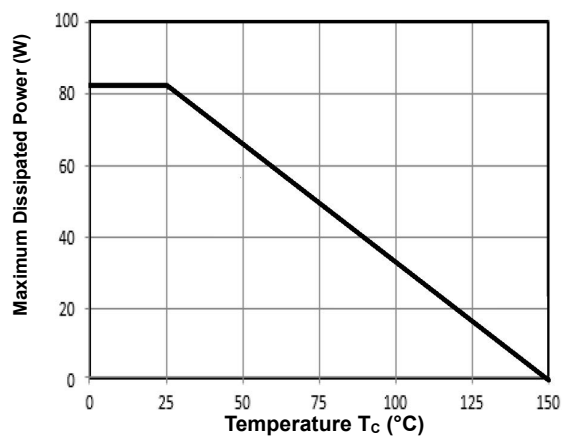


FIG.8- Maximum Power Dissipation Derating vs Case Temperature

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